



Phase Control Thyristor

DS6052-1 April 2011 (LN28263)

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V _{DRM} and V _{RRM} V	Conditions
DCR5110M34 DCR5110M32 DCR5110M30 DCR5110M28 DCR5110M26 DCR5110M24	3400 3200 3000 2800 2600 2400	$\begin{split} T_{vj} = -40^{\circ}\text{C to } 125^{\circ}\text{C}, \\ I_{DRM} = I_{RRM} = 400\text{mA}, \\ V_{DRM}, V_{RRM} t_p = 10\text{ms}, \\ V_{DSM} \& V_{RSM} = \\ V_{DRM} \& V_{RRM} +100V \\ respectively \end{split}$

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR5110M34

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	3400 V
$I_{T(AV)}$	5110 A
I _{TSM}	69000 A
dV/dt*	1000 V/µs
dI/dt	250 A/μs

* Higher dV/dt selections available

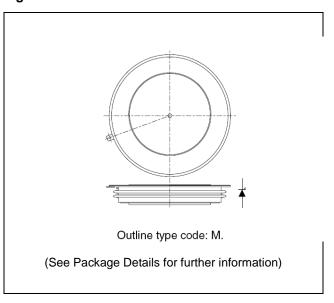


Fig. 1 Package outline



CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units	
Double Si	Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	5110	А	
I _{T(RMS)}	RMS value	-	8020	А	
I _T	Continuous (direct) on-state current	-	7230	А	

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	t 10ms half sine, T _{case} = 125°C		kA
l ² t	I ² t for fusing	$V_R = 0$	23.81	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	DC		0.005	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Double side cooled	DC		0.0015	°C/W
T_{vj}	Virtual junction temperature	Blocking V _{DRM} / _{VRRM}			125	°C
T _{stg}	Storage temperature range			-40	140	°C
F _m	Clamping force			80	100	kN



DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
I _{RRM} /I _{DRM}	Peak reverse and off-state current	At V _{RRM} /V _{DRM} , T _{case} = 125°C		-	400	mA
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V _{DRM} , T _j = 125°C, gate open		1000	-	V/µs
dl/dt	Rate of rise of on-state current	From 67% V _{DRM} to 4000A	Repetitive 50Hz	-	250	A/µs
		Gate source 30V, 10Ω ,	Non-repetitive	-	1000	A/µs
		$t_r < 0.5 \mu s, T_j = 125 ^{\circ} C$				
V _T	On-state voltage	I _T = 3000A, T _{case} = 125°C			1.21	V
V _{T(TO)}	Threshold voltage	T _{case} = 125°C		-	0.86	V
r _T	On-state slope resistance	T _{case} = 125°C		-	0.115	mΩ
t _{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10Ω		-	3.0	μs
	,	$t_r = 0.5 \mu s, T_j = 25^{\circ}C$				
tq	Turn-off time	$T_j = 125$ °C, $V_R = 100$ V, $dI/dt = 1.5$ A/ μ s,		-	600	μs
		dV _{DR} /dt = 20V/μs linear to 67% V _{DRM}				
Qs	Stored charge	$I_T = 2000A$, tp = 1000us, $T_j = 125$ °C, dl/dt =1.5A/µs,		-	4000	μC
I _{RR}	Reverse recovery current			-	100	Α
IL	Latching current	$T_j = 25$ °C,		-	1	Α
I _H	Holding current	T _j = 25°C,		-	200	mA

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	3	V
V_{GD}	Gate non-trigger voltage	At 40% V _{DRM} , T _{case} = 125°C	TBD	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	300	mA
I _{GD}	Gate non-trigger current	At 40% V _{DRM} , T _{case} = 125°C	TBD	mA



CURVES

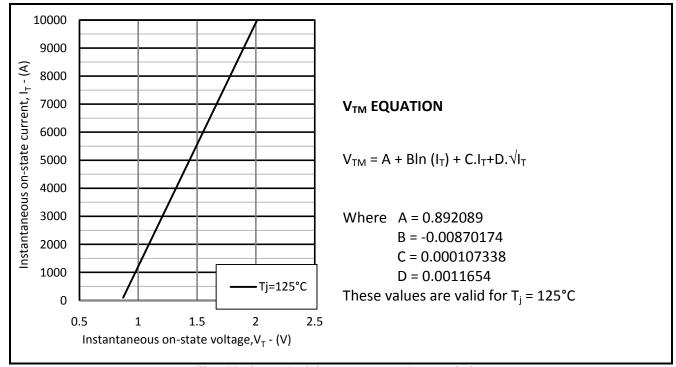


Fig.2 Maximum &minimum on-state characteristics

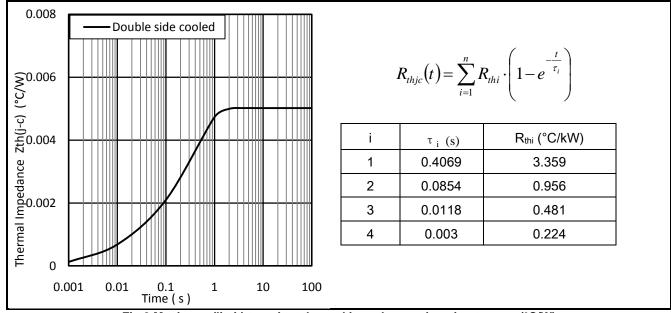
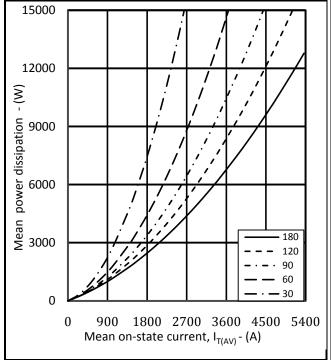


Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)





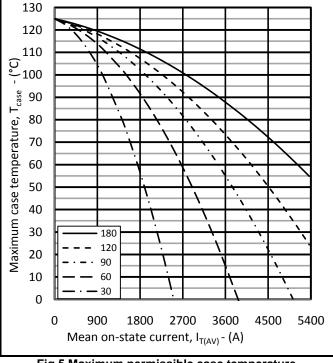


Fig.4 On-state power dissipation – sine wave

Fig.5 Maximum permissible case temperature, double side cooled – sine wave

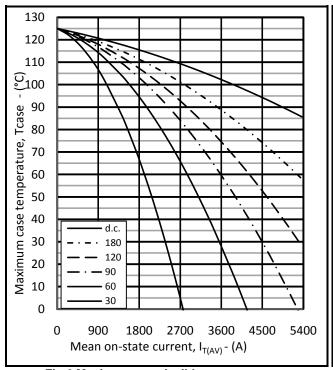


Fig.6 Maximum permissible case temperature, double side cooled – rectangular wave

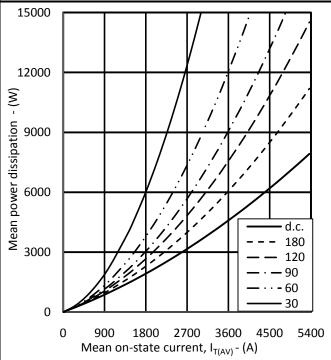
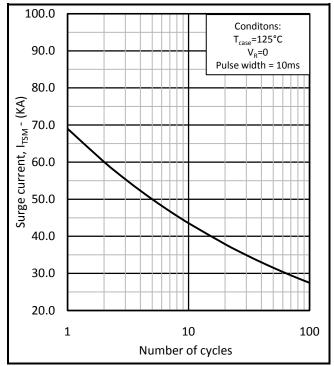


Fig.7 On-state power dissipation - rectangular wave





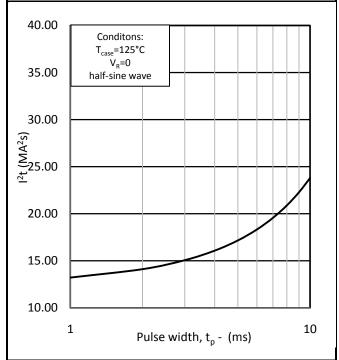


Fig.8 Multi-cycle surge current

Fig.9 Single-cycle I2t

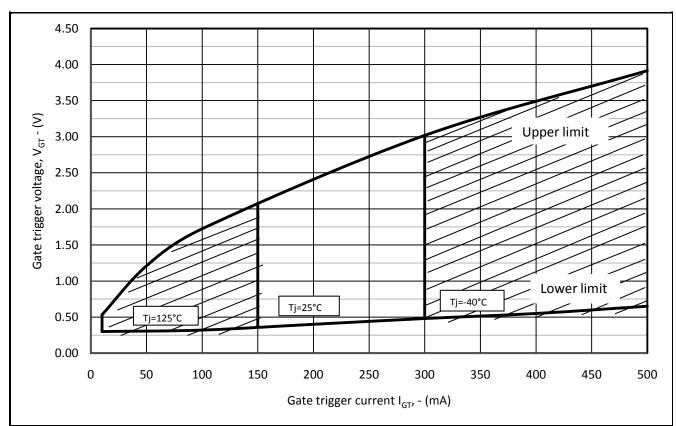


Fig.10 Gate characteristics



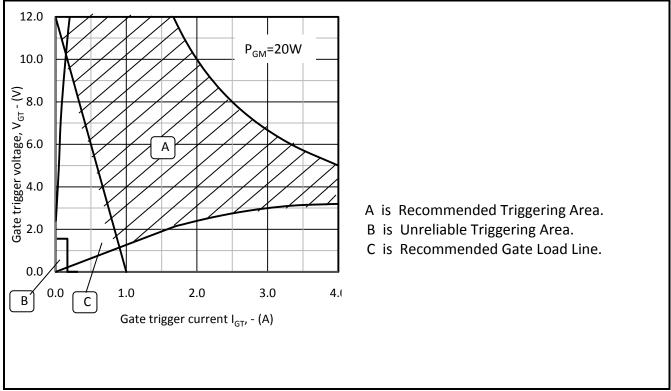


Fig.11 Gate characteristics



PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

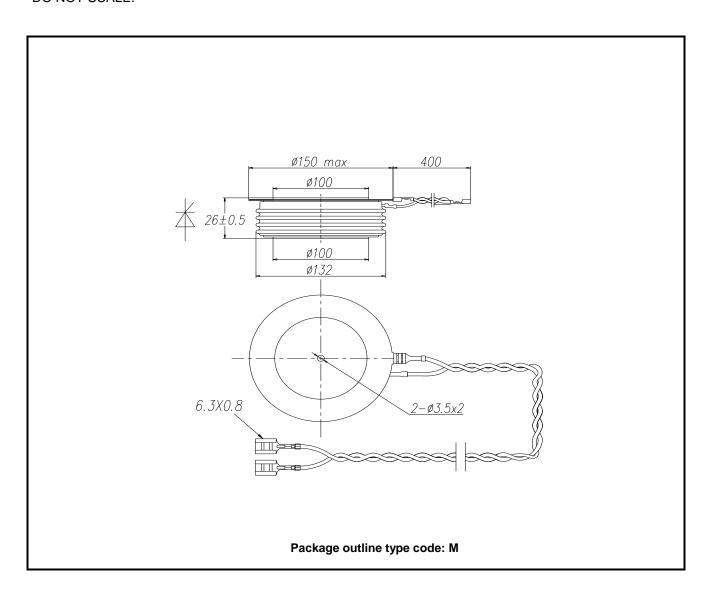


Fig.12 Package outline



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